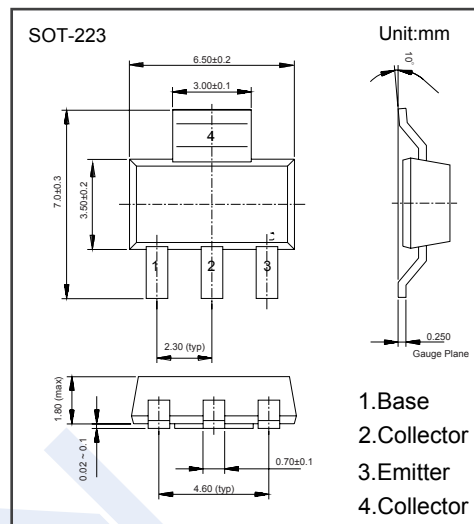


PNP Transistors

FZT1151A (KZT1151A)

■ Features

- Collector Current Capability $I_C = -3A$
- Collector Emitter Voltage $V_{CE0} = -40V$
- Low Saturation voltage



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-45	V
Collector - Emitter Voltage	V_{CEO}	-40	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-3	A
Collector Current - Pulse	I_{CP}	-5	
Base Current	I_B	-500	mA
Collector Power Dissipation	P_C	2.5	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

PNP Transistors

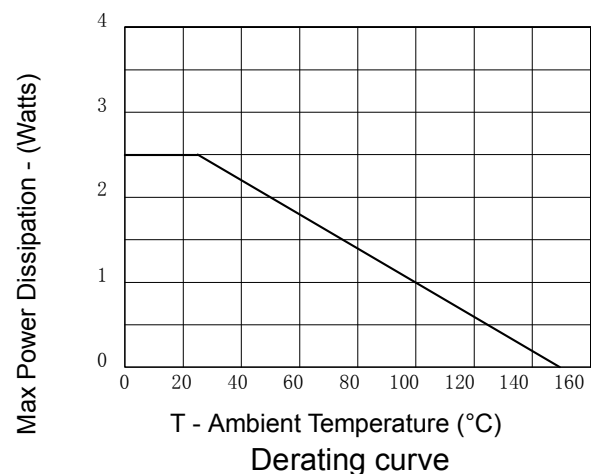
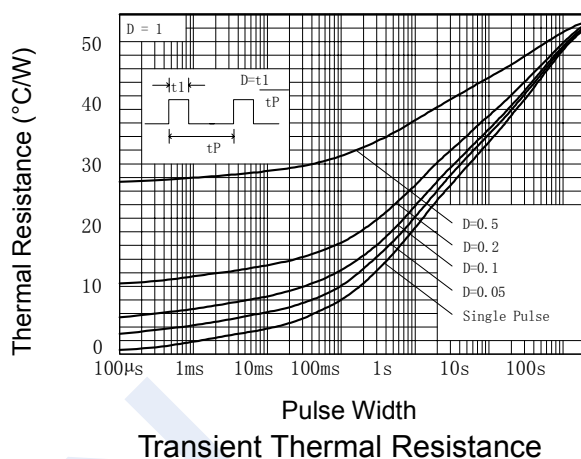
FZT1151A (KZT1151A)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\ \mu\text{A}$, $I_E = 0$	-45			V
Collector- emitter breakdown voltage	V_{CES}	$I_C = -100\ \mu\text{A}$, $I_B = 0$	-45			
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -10\ \text{mA}$, $I_B = 0$	-40			
Collector- emitter breakdown voltage	V_{CEV}	$I_C = -100\ \mu\text{A}$, $V_{EB} = 1\text{V}$	-40			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100\ \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -36\ \text{V}$, $I_E = 0$			-100	nA
Collector-emitter cut-off current	I_{CES}	$V_{CE} = -32\ \text{V}$, $I_B = 0$			-100	
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$ (Note.1)			-90	mV
		$I_C = -0.5\ \text{A}$, $I_B = -3\text{mA}$ (Note.1)			-180	
		$I_C = -1\ \text{A}$, $I_B = -20\text{mA}$ (Note.1)			-220	
		$I_C = -1.8\ \text{A}$, $I_B = -70\text{mA}$ (Note.1)			-260	
		$I_C = -3\ \text{A}$, $I_B = -250\text{mA}$ (Note.1)			-300	
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -3\ \text{A}$, $I_B = -250\text{mA}$ (Note.1)			-1.1	V
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	$V_{CE} = -2\text{V}$, $I_C = -3\text{A}$ (Note.1)			-1	
DC current gain (Note.1)	$h_{FE(1)}$	$V_{CE} = -2\text{V}$, $I_C = -10\text{mA}$	270			
	$h_{FE(2)}$	$V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$	250		800	
	$h_{FE(3)}$	$V_{CE} = -2\text{V}$, $I_C = -2\ \text{A}$	180			
	$h_{FE(4)}$	$V_{CE} = -2\text{V}$, $I_C = -3\ \text{A}$	100			
	$h_{FE(5)}$	$V_{CE} = -2\text{V}$, $I_C = -5\ \text{A}$		45		
Switching Times	t_{on}	$I_C = -2\text{A}$, $I_B = -20\text{mA}$, $V_{CC} = -30\text{V}$		170		ns
	t_{off}	$I_C = -2\text{A}$, $I_B = \pm 20\text{mA}$, $V_{CC} = -30\text{V}$		460		
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$		40		pF
Transition frequency	f_r	$V_{CE} = -10\text{V}$, $I_C = -50\text{mA}$, $f = 50\text{MHz}$		145		MHz

Note.1: Pulse width=300 μs . Duty cycle $\leq 2\%$

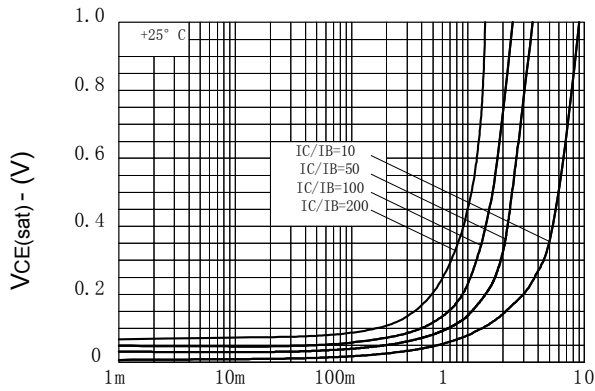
■ Typical Characteristics



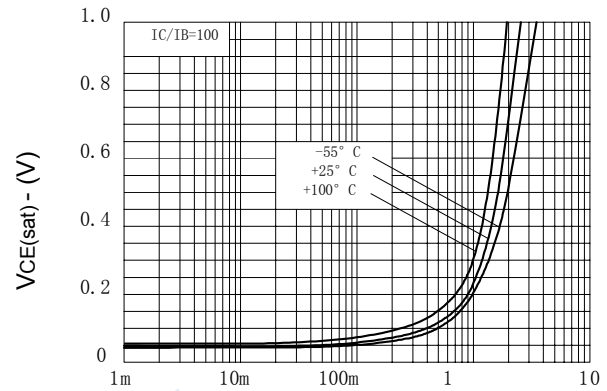
PNP Transistors

FZT1151A (KZT1151A)

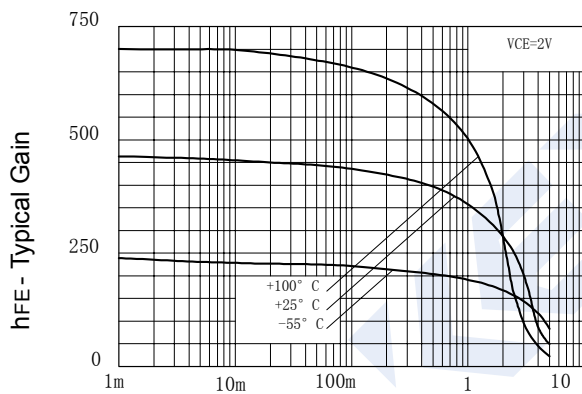
■ Typical Characteristics



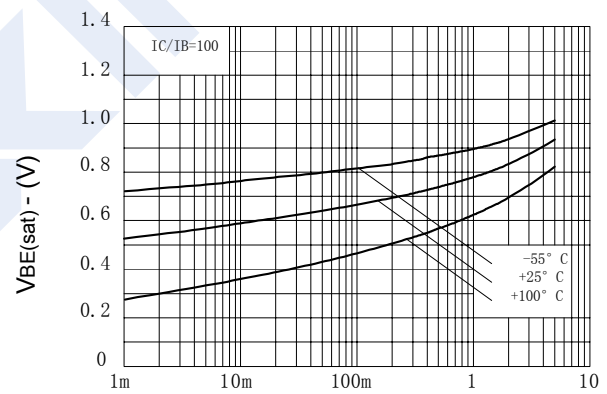
I_C - Collector Current (A)
 $V_{CE(sat)}$ v I_C



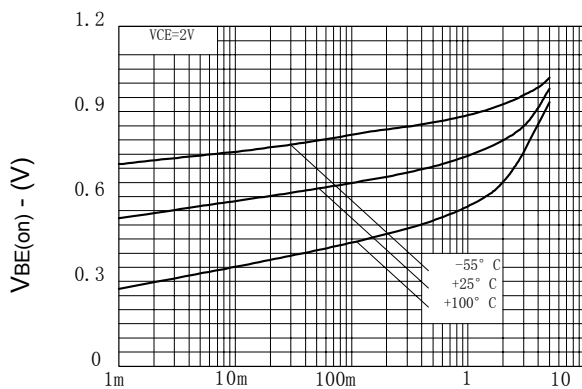
I_C - Collector Current (A)
 $V_{CE(sat)}$ v I_C



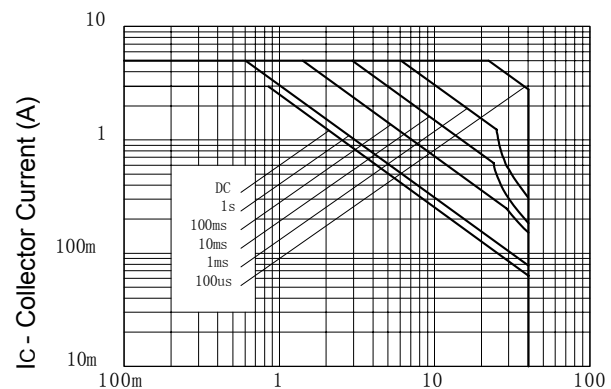
I_C - Collector Current (A)
 h_{FE} v I_C



I_C - Collector Current (A)
 $V_{BE(sat)}$ v I_C



I_C - Collector Current (A)
 $V_{BE(on)}$ v I_C



V_{CE} - Collector Emitter Voltage (V)
Safe Operating Area